



肖特基二極管

SB8150D - SB8200D

Case: TO-263 8.0A High Voltage SMD Dual Schottky Barrier Rectifier

Feature

- ◆ Schottky Barrier Chip
- ◆ Guard Ring Die Construction For Transient Protection
- ◆ Low Forward Voltage Drop
- ◆ Low Power Loss, High Efficiency
- ◆ High Surge Current Capability
- ◆ For Use in Low Voltage, High Frequency Inverters, Free Wheeling and Polarity Protection Applications.

Figure



Mechanical Data

- ◆ Case: D²PAK/TO-263, Molded Plastic
- ◆ Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- ◆ Polarity: See Diagram
- ◆ Weight: 1.7 grams (approx)
- ◆ Mounting Position: Any
- ◆ Marking: Type Number
- ◆ Lead Free: For RoHS / Lead Free Version Add "-LF" Suffix to part Number.

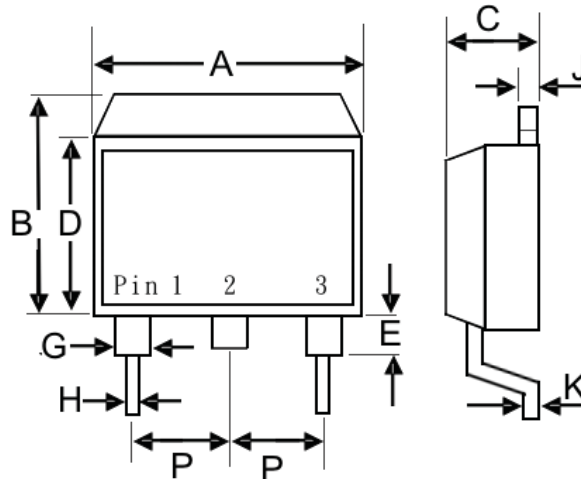
Electrical Symbol



Dimension

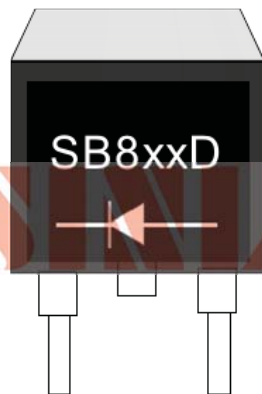
Case: D²PAK/TO-263 (mm)

Dim.	Min.	Max.
A	9.8	10.4
B	9.6	10.6
C	4.4	4.8
D	8.5	9.1
E	2.8	---
G	1.0	1.4
H	---	0.9
J	1.2	1.4
K	0.3	0.7
P	2.35	2.75

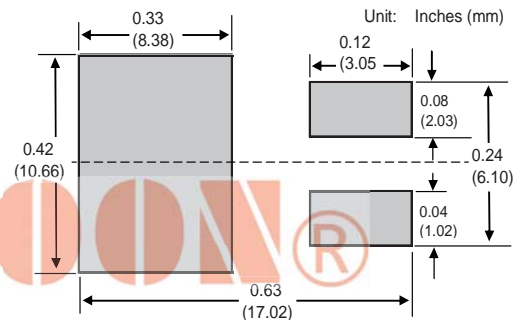


Marking Information

- SB8xxD = Device Number
- xx = See Page 2 SB Part 150, 200.
- Polarity = As Marked Body



Recommended Footprint



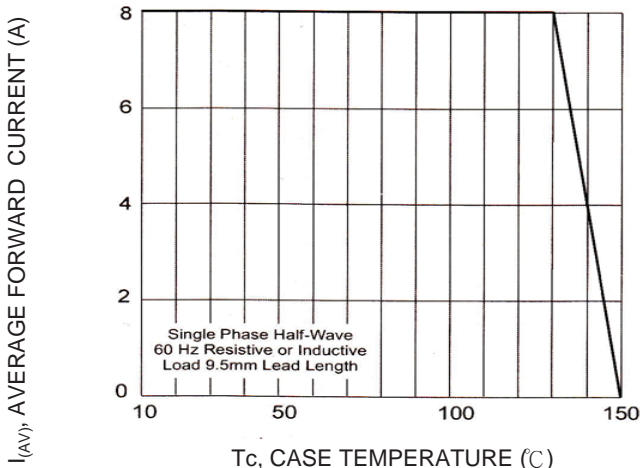
□ **Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified**

Single Phase, half wave, 60Hz, resistive or inductive load For capacitive load, derate current by 20%.

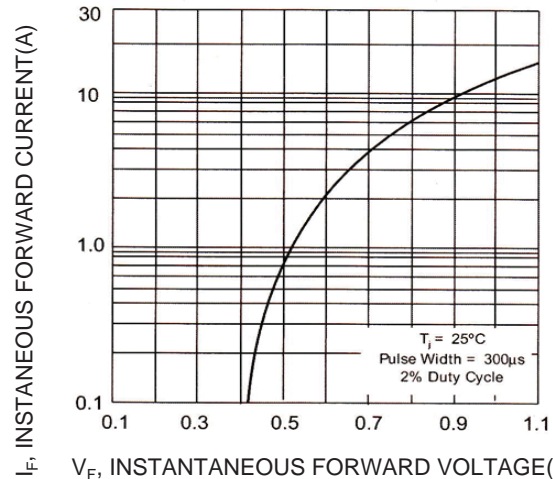
Characteristics	Symbol	SB8150D	SB8200D	Unit
Peak Repetitive Reverse Voltage	V _{RRM}			
Working Peak Reverse Voltage	V _{RWM}	150	200	V
DC Blocking Voltage	V _R			
RMS Reverse Voltage	V _{R(RMS)}	105	140	V
Average Rectified Output Current @T _C =130°C	I _O	8.0	8.0	A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC)	I _{FSM}	150	150	A
Forward Voltage @I _F =8.0A	V _{FM}	0.92	0.92	V
Peak Reverse Current @T _A = 25°C	I _{RM}	0.5		mA
At Rated DC Blocking Vol. @T _A =100°C		50		
Typical Junction Capacitance (Note 1)	C _J	350		pF
Typical Thermal Resistance (Note 2)	R _{θJC}	3.0		°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150		°C

Note 1: Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

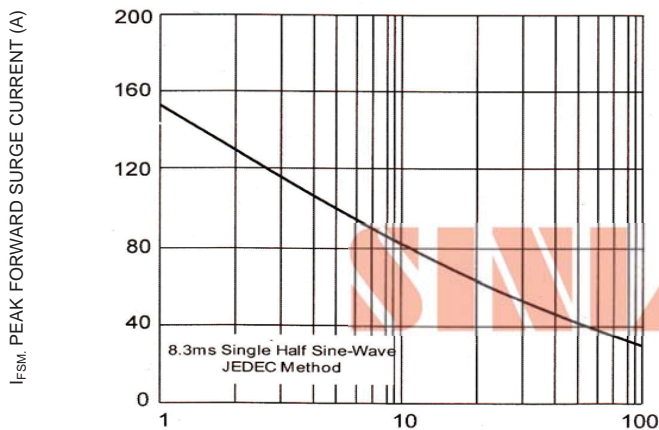
Note 2: Mounfed on minimum recommended pad size on FR-4 board.



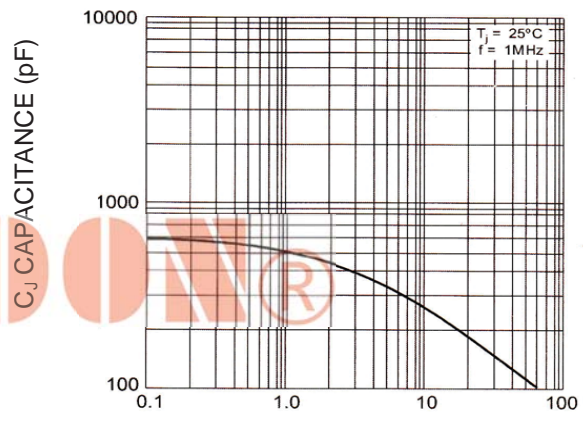
T_c, CASE TEMPERATURE (°C)
Fig-1 Forward and Current Derating Curve



V_F, INSTANTANEOUS FORWARD VOLTAGE (V)
Fig-2 Typical Forward Characteristic:



NUMBER OF CYCLES AT 60 Hz
Fig-3 Maximum Non-Repetitive Paek FWD Surge Current



V_R, REVERSE VOLTAGE (V)
Fig-4 Typical Junction Capacitance

SINLOON®

肖特基二極管

SB8150D - SB8200D

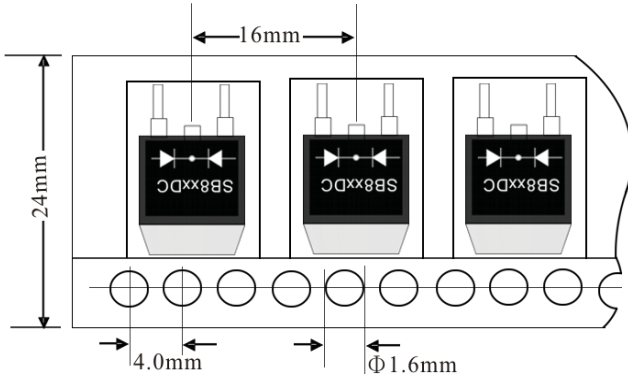
Case: TO-263 8.0A High Voltage SMD Dual Schottky Barrier Rectifier

□ Packaging Information

Reel Dimension (mm)	Quantity (Pcs)	Inner Box Size LxWxH (mm)	Quantity (Pcs)	Carton Size LxWxH (mm)	Quantity (Pcs)	Gross Weight
330	800	340x337x45	1600	370x370x420	6400	15.0Kg

Note: 1. Paper reel. White or gray color,
2. Components are packed in accordance with EIA standard 481-1 and 481-2

Paper Tape



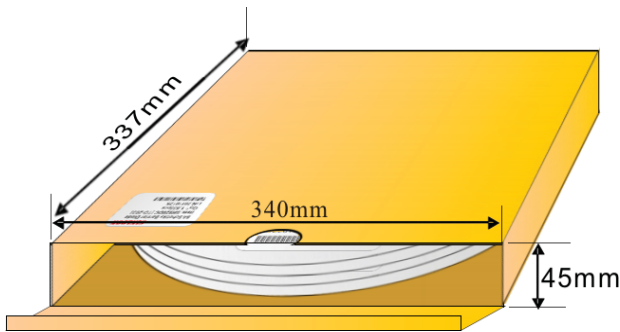
Reel Package

Size: 330 mm



Quantity: 800 pcs

Inner Box



Quantity: 16,000 pcs

Cartons Package



Quantity: 6,400 Pcs

SINLOON®

※美隆公司產品規格及其特性參數的改變或更新恕不另行通知。

※Mayloon characteristic parameters of electronic product specification changes or updates without notice to improve。

